

**FEATURES**

- Maximum Gate Trigger Current: 2, 20 or 200 $\mu$ A
- Tight Gate Trigger Voltage Range: .44 to .6V
- Voltage Ratings: to 400V
- Specified for dv/dt and Switching Time

**DESCRIPTION**

This data sheet describes Microsemi's AD Series 1.6A SCRs designed for medium-current control and sensing applications. Units are available in a complete range of blocking voltages from 60 to 400 volts.

The AD100 series offers a maximum gate trigger current of 2.0 microamps making it the most sensitive device of its type. The AD107 series has a maximum  $I_{GT}$  of 20 $\mu$ A while this parameter is specified at 200 $\mu$ A for the AD114 series.

**ABSOLUTE MAXIMUM RATINGS**

	AD100 AD107 AD114	AD101 AD108 AD115	AD102 AD109 AD116	AD103 AD110 AD117	AD104 AD111 AD118
Repetitive Peak Off-State Voltage, $V_{DRM}$	60V	100V	200V	300V	400V
Repetitive Peak Reverse Voltage, $V_{RRM}$	60V	100V	200V	300V	400V
Non-Repetitive Peak Reverse Voltage, $V_{RSM}$	80V	150V	300V	400V	500V
Non-Repetitive Peak Off-State Voltage, $V_{DSM}$			500V		
D.C. On-State Current, $I_T$					
75°C Ambient			450mA		
85°C Case			1.6A		
Repetitive Peak On-State Current, $I_{TRM}$			up to 30A		
Peak One Cycle Surge (Non-Rep.) On-State Current, $I_{TSM}$			15A		
Peak Gate Current, $I_{GM}$			250mA		
Average Gate Current, $I_{G(AV)}$			25mA		
Reverse Gate Voltage, $V_{GR}$			6V		
Operating and Storage Temperature Range			-65°C to +150°C		

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**MECHANICAL SPECIFICATIONS**

AD100-AD104    AD107-AD111    AD114-AD118

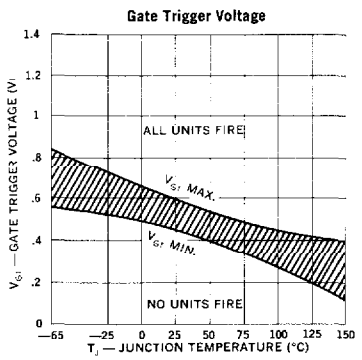
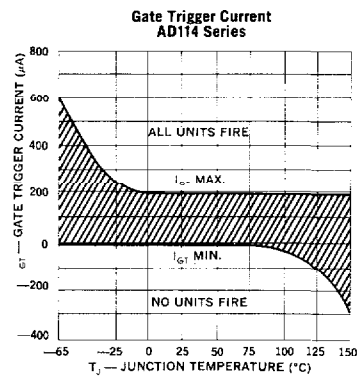
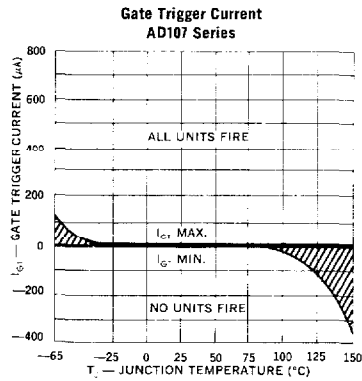
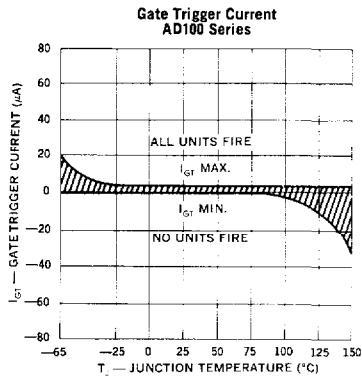
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A	305-335	7.75-8.51
B	335-370	8.51-9.40
C	240-250	6.35-6.60
D	.010-.030	.25-.75
E	5 MIN.	12.70 MIN.
F	.017 ± .002 .001	.432 ± .051 .025
G	.200	5.08
H	.100	2.54
J	.031 ± .003	.79 ± .08
K	.023-.045	.74-1.14
L	.100	2.54

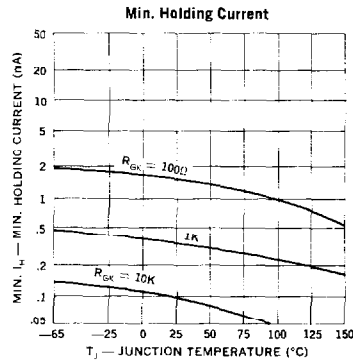
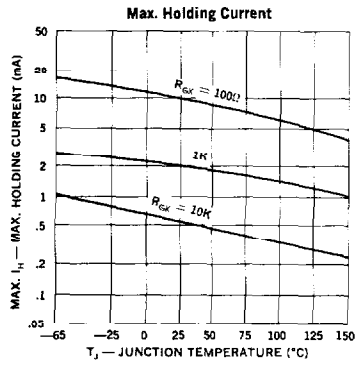
TO-205AD (TO-39)

**ELECTRICAL SPECIFICATIONS (at 25°C unless noted)**

Parameter	Symbol	Min.	Typical	Max.	Units	Test Conditions
<b>SUBGROUP 1</b>						
Visual & Mechanical						
<b>SUBGROUP 2 (25°C TESTS)</b>						
Off-State Current	$I_{DRM}$	—	.01	0.1	$\mu A$	$R_{GK} = 1K, V_{DRM} = \text{Rating}$
Reverse Current	$I_{RRM}$	—	.01	0.1	$\mu A$	$R_{GK} = 1K, V_{RRM} = \text{Rating}$
Reverse Gate Current	$I_{GR}$	—	0.1	0.2	$\mu A$	$V_{GR} = 2V$
Gate Trigger Current	$I_{GT}$	—	—	—	—	$R_{GS} = 10K, V_D = 5V$
AD100-104		—	0.2	2.0	$\mu A$	
AD107-111		—	2.0	20	$\mu A$	
AD114-118		—	20	200	$\mu A$	
Gate Trigger Voltage	$V_{GT}$	0.44	0.52	0.60	V	$R_{GS} = 100\Omega, V_D = 5V$
On-State Voltage	$V_T$	—	1.1	1.5	V	$I_T = 1.0 \text{ Amp (pulse)}$
Holding Current	$I_H$	0.3	0.5	2.0	mA	$R_{GK} = 1K$
<b>SUBGROUP 3 (25°C TESTS)</b>						
On-State Voltage-Critical Rate of Rise	$dv/dt$	50	100	—	V/ $\mu S$	$R_{GK} = 1K, V_D = 30V$
Gate Trigger-on Pulse Width	$t_{pg} \text{ (on)}$	—	0.5	2.0	$\mu S$	$I_G = 10mA, I_T = 1A, V_D = 30V$
Delay Time	$t_d$	—	0.6	—	$\mu S$	$I_G = 10mA, I_T = 1A, V_D = 30V$
Rise Time	$t_r$	—	0.4	—	$\mu S$	$I_G = 10mA, I_T = 1A, V_D = 30V$
Circuit Commutated Turn-off Time	$t_q$	—	20	50	$\mu S$	$I_T = 1A, I_R = 1A, R_{GK} = 1K$
<b>SUBGROUP 4 (125°C TESTS)</b>						
Off-State Current	$I_{DRM}$	—	10	100	$\mu A$	$R_{GK} = 1K, V_{DRM} = \text{Rating}$
Reverse Current	$I_{RRM}$	—	30	100	$\mu A$	$R_{GK} = 1K, V_{RRM} = \text{Rating}$
Gate Trigger Voltage	$V_{GT}$	0.15	0.2	—	V	$R_{GS} = 100\Omega, V_D = 5V$
Holding Current	$I_H$	0.2	0.4	1.5	mA	$R_{GK} = 1K$

Note: Blocking voltage ratings apply over the full operating temperature range, provided the gate is connected to the cathode through a resistor, 1000 ohms or smaller, or other adequate bias is used.





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